

Background

Evidence suggests that a high density of dislocations correlates with poor optoelectronic performance in semiconductor based devices.

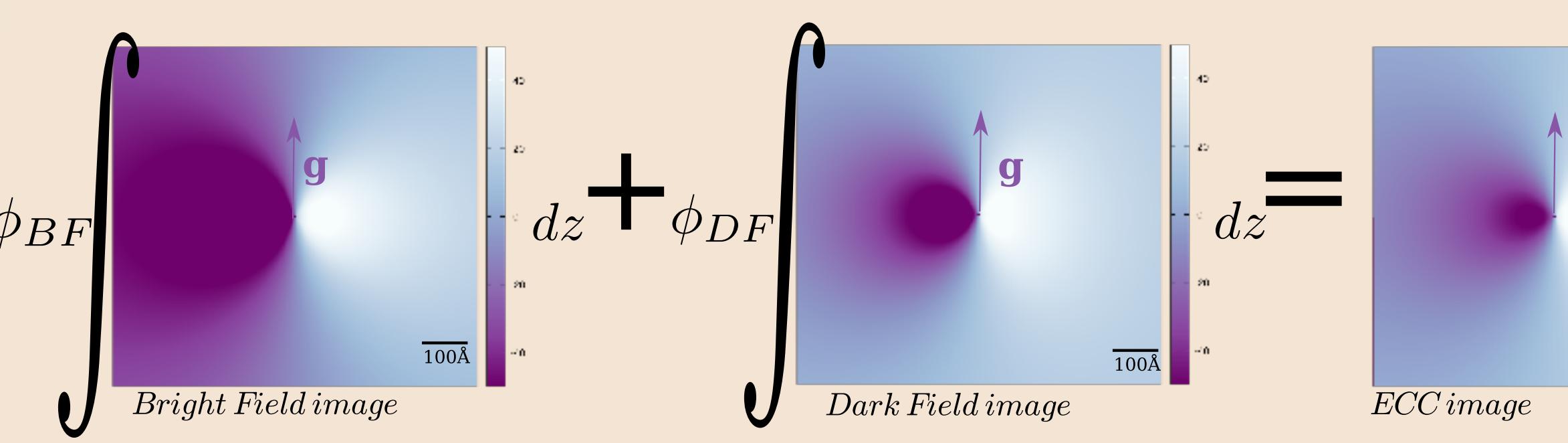
Threading dislocations (TDs) are line defects that run through the material and reach its surface. They are believed to act as non-radiative recombination centres affecting the luminescence output efficiency.

Dislocations bend the lattice of the perfect crystal introducing **local strain** providing a characteristic marker that can be observed. The electron microscope is one tool that measures this marker.

Electron channelling contrast imaging (ECCI) is a non-destructive scanning electron microscope technique that can provide material structural information by measuring the intensity of the backscattered electrons [1]. It is the purpose of this study to provide a model of the threading dislocation contrast thus observed.

ECC images

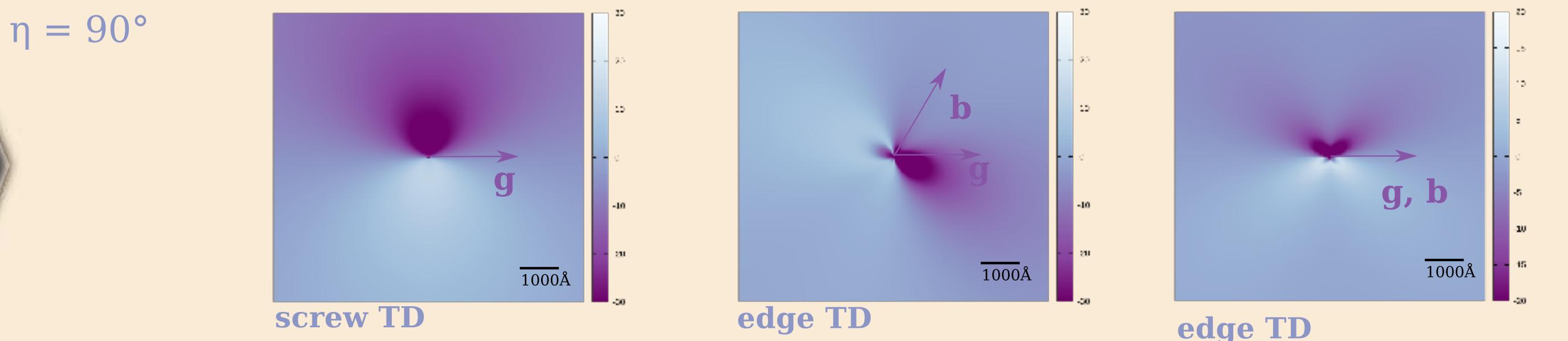
Using the assumption that the backscattered signal comes from a single inelastic scattering event (Rossouw et al.[6]), the ECC image is then calculated as the weighted sum of the integrated BF and DF signal. The weighting factor is the cross section for impact ionisation (ϕ) for the given detector angle (α).



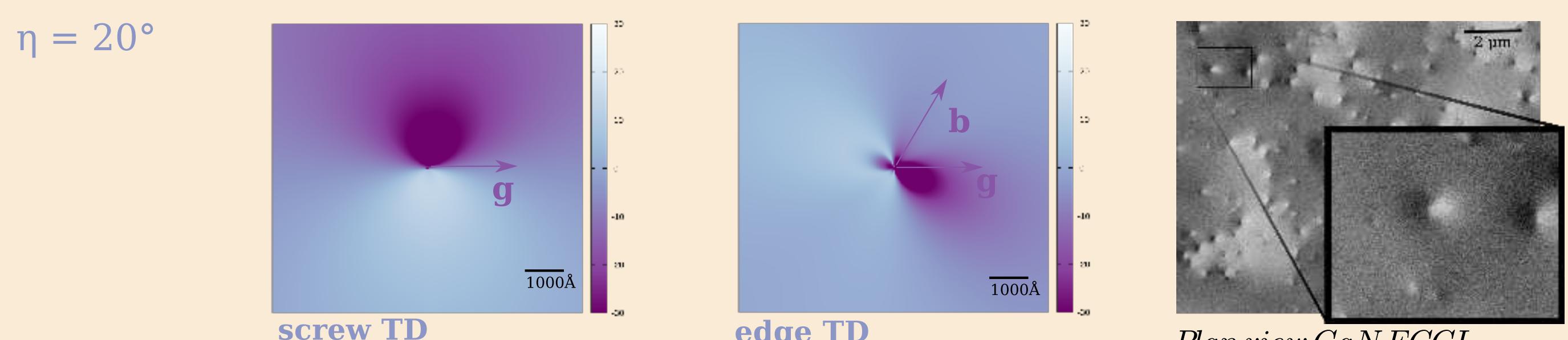
screw dislocation along GaN(0001)

[11-20] reflection
 $t = 0.5 \xi g$
 $w = 0$
 $\alpha_{\text{detector}} = 40^\circ$
 $\eta_{\text{sample}} = 90^\circ$

Backscatter geometry



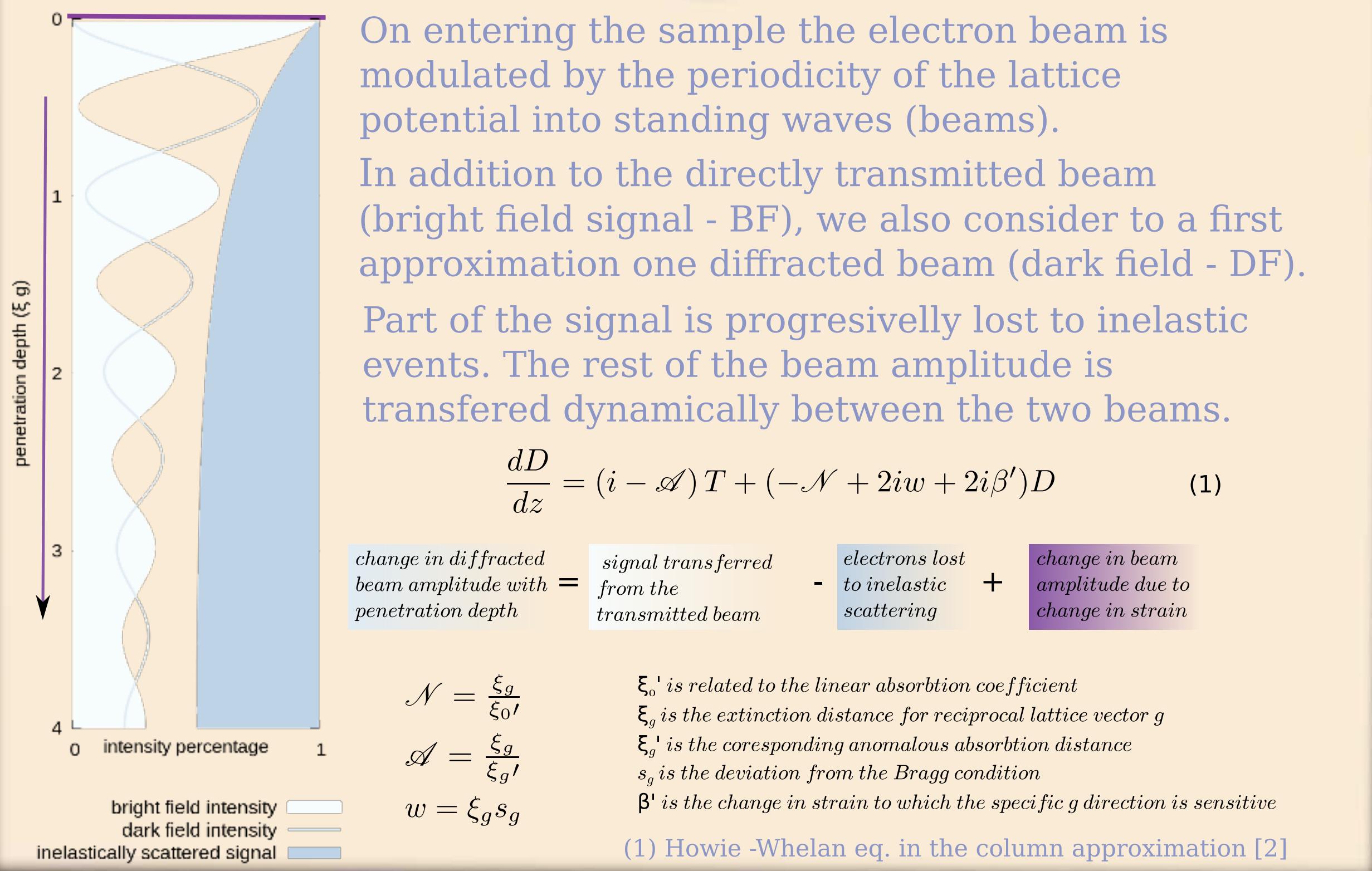
Forescatter geometry



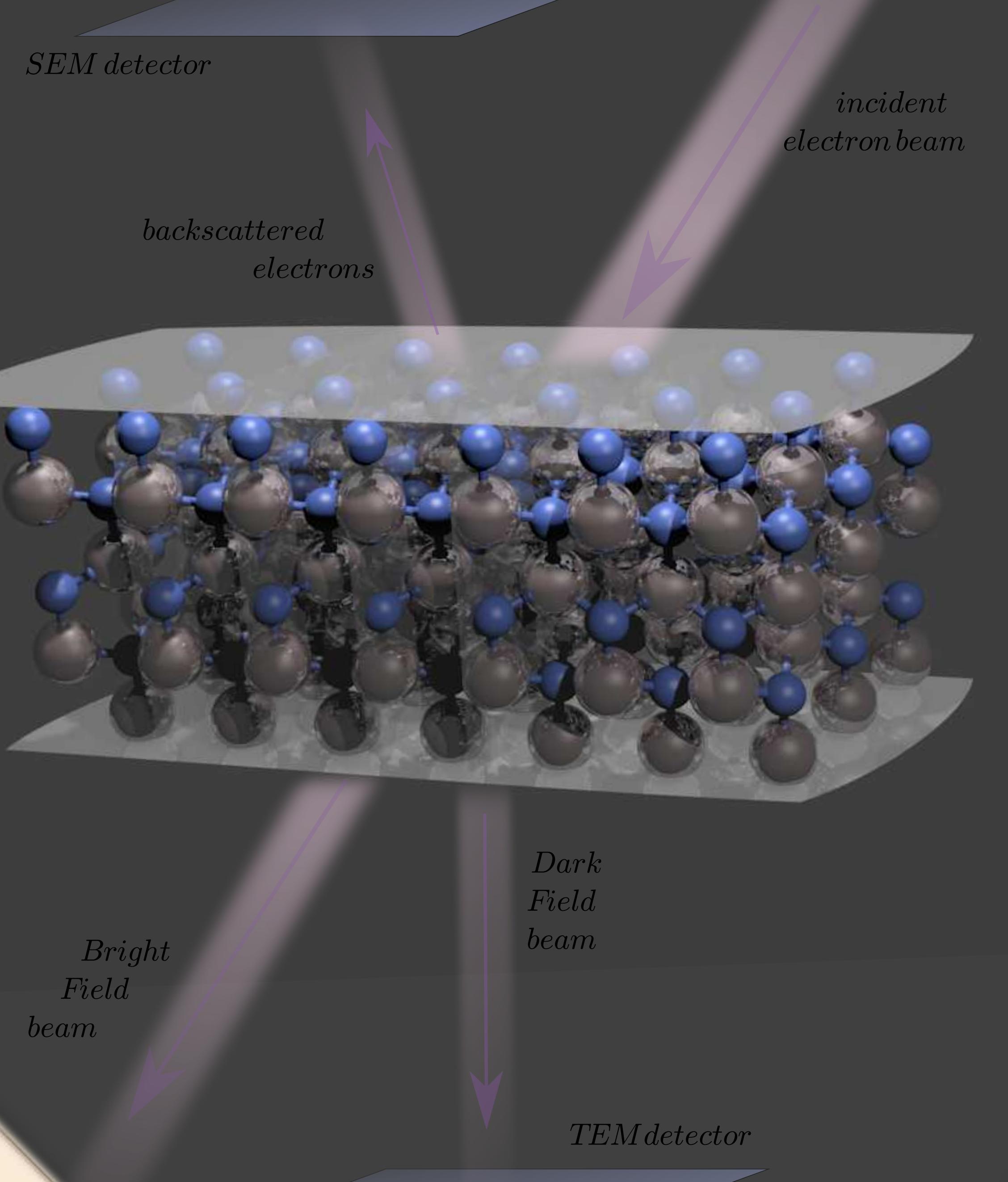
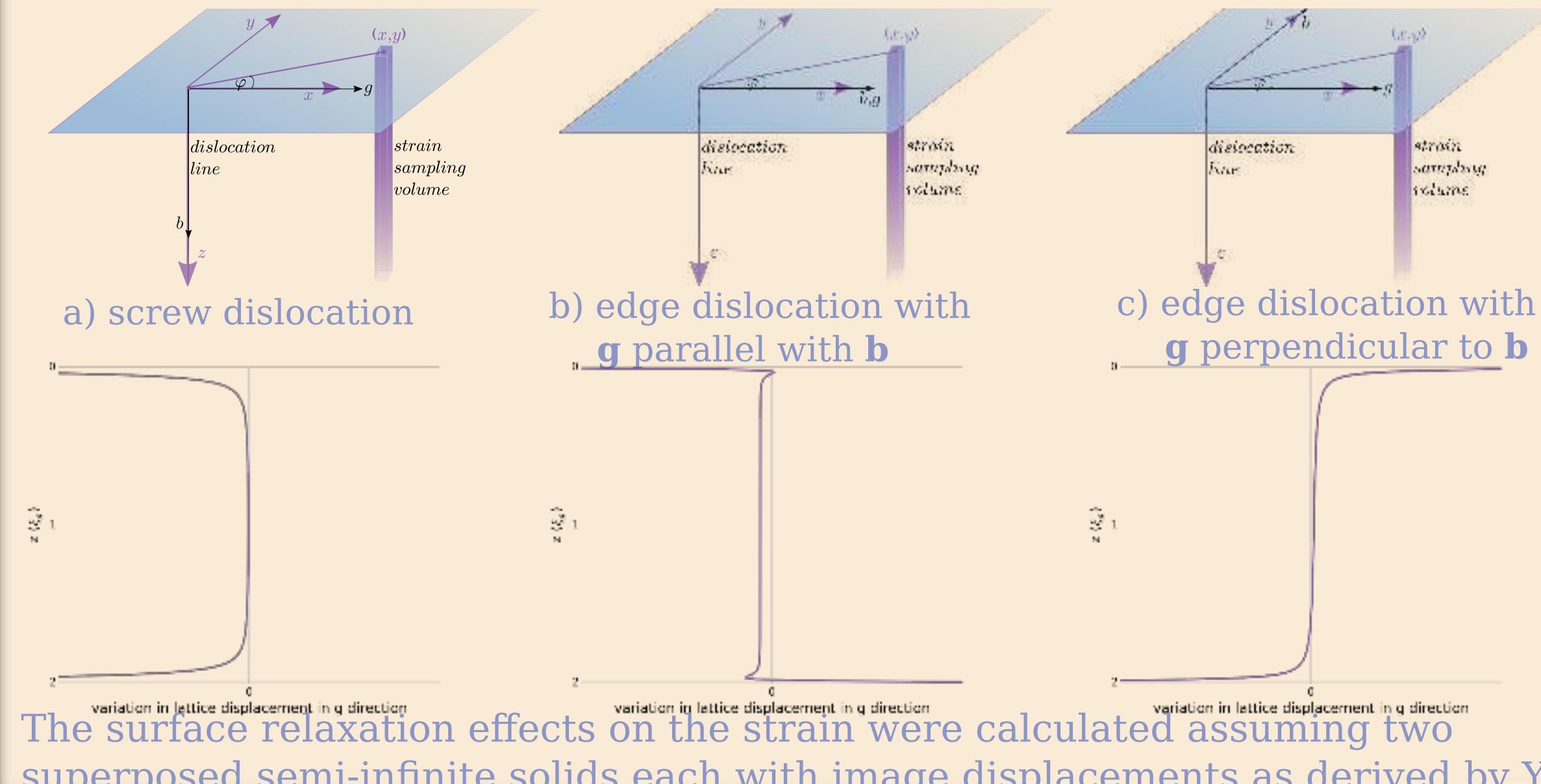
Plan view GaN ECCI.
By permission of Allehiani Nouf
Mohammad

Theoretical model of contrast produced by surface normal TDs as observed by ECCI

Model



Strain variation through cubic crystal thin sample



References:

- [1] Kumar, N. G., et al., 2012, *Phys. Rev. Lett.*, **108**, 13
- [2] Howie, A., and Whelan, M. J., 1961, *Proc. Roy. Soc. A*, **263**, 217
- [3] Yoffe, E. H., 1961, *Phil. Mag.*, **6**, 1147
- [4] Tunstall, W. J. and Hirsch, P. B., 1964 *Phil. Mag.*, **9**, 97
- [5] Follstaedt, D. M., et al., 2003, *Appl. Phys. Lett.* **83**, 4797
- [6] Rossouw, P. R., et al., 1994, *Phil. Mag. A*, **70**, 985

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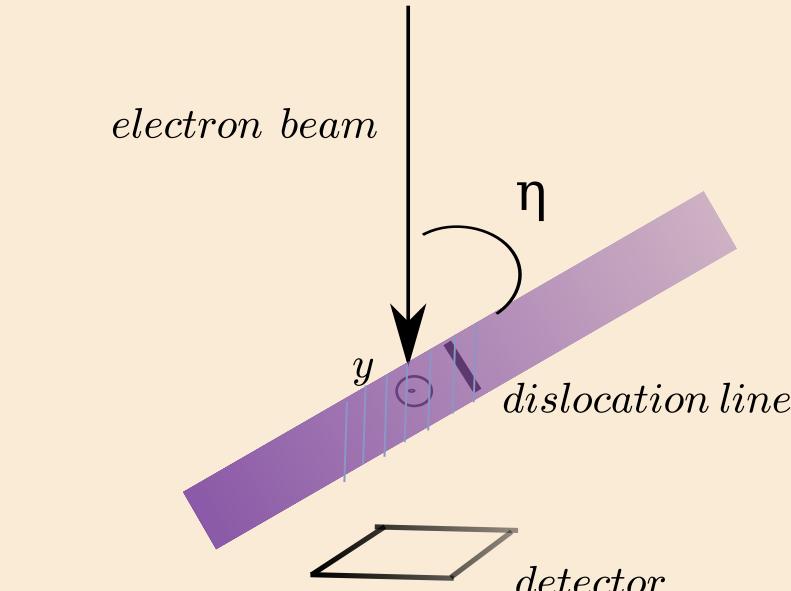
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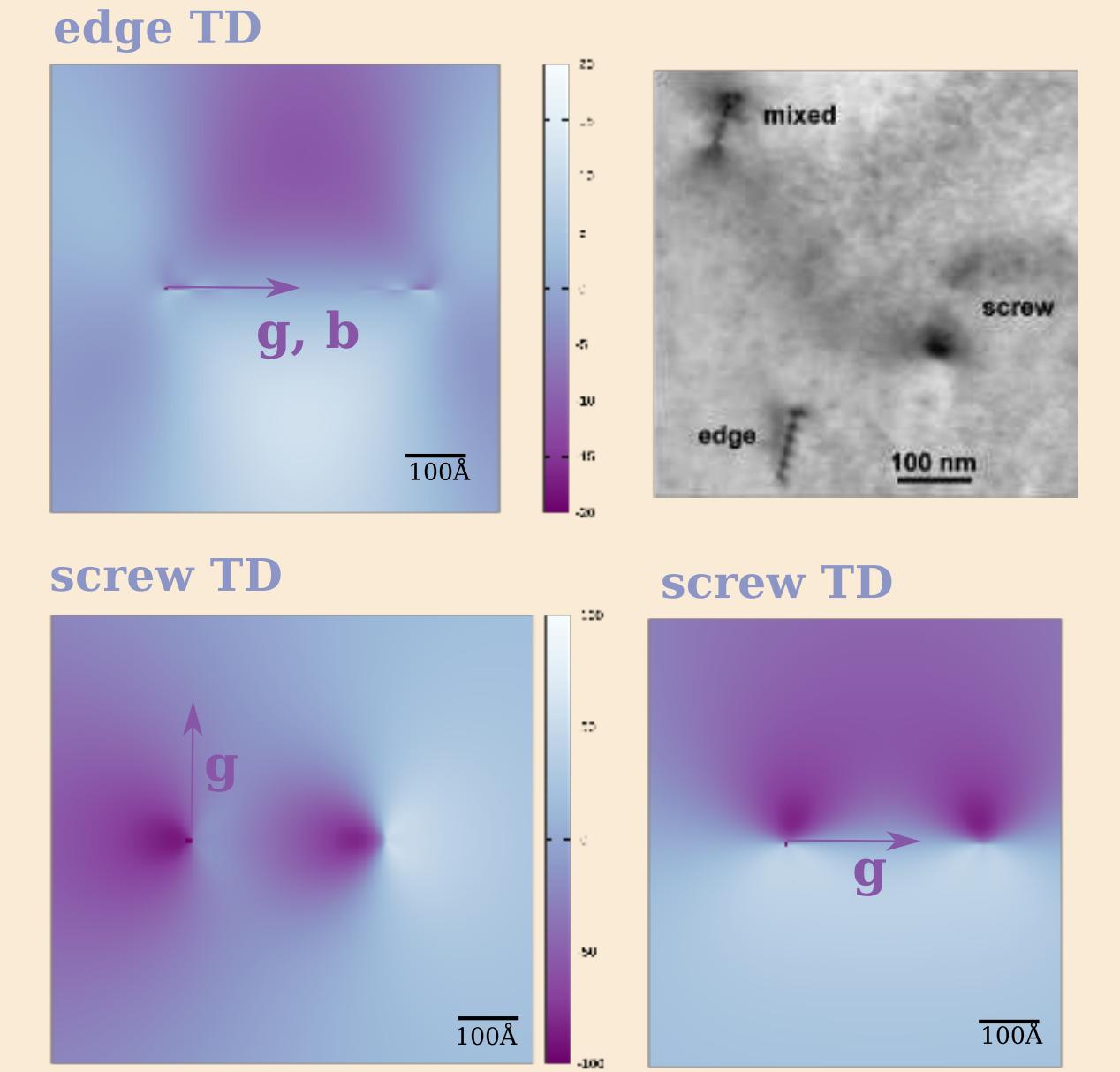


Tilting the sample

[0001] orientation
 $\eta = 78^\circ$
 $y = (11-20)$
 $t = 5 \xi g$
 $w = 0.2$



Can be easily modelled by rotating the coordinate system of the strain field by an angle η with respect to the y -axis. The integrating columns will remain along the direction of the incident beam. The simulated images show good qualitative resemblance to the experimental work of Follstaedt et al. [5].



TEM bright field images

